

ABSTRACT OF THE DISCLOSURE

[1124] An exemplary NAND string memory array includes at least one plane of memory cells, said memory cells comprising thin film modifiable conductance switch devices and which cells are arranged in a plurality of series-connected NAND strings, said NAND strings including a series select device at each end thereof. Another exemplary NAND string memory array includes a group of more than four adjacent NAND strings within the same memory block each associated with a respective global bit line not shared by the other NAND string of the group. Another exemplary NAND string memory array includes NAND strings on identical pitch as their respective global bit lines.